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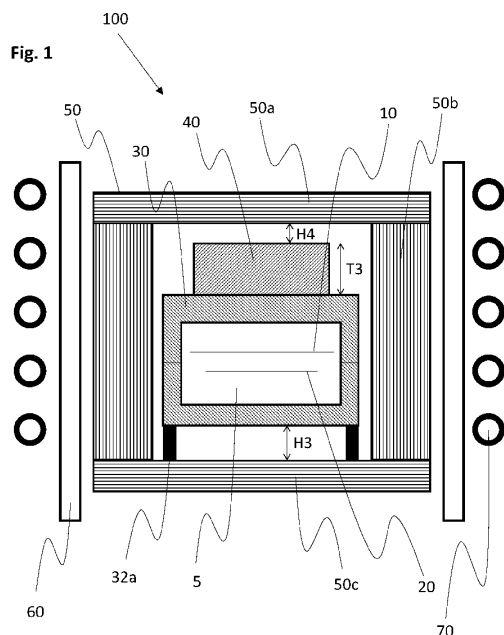
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(54) Title: SYSTEM AND METHOD OF PRODUCING MONOCRYSTALLINE LAYERS ON A SUBSTRATE



(57) Abstract: A system (100) for producing an epitaxial monocrystalline layer on a substrate (20) comprising: an inner container (30) defining a cavity (5) for accommodating a source material (10) and the substrate (20); an insulation container (50) arranged to accommodate the inner container (30) therein; an outer container (60) arranged to accommodate the insulation container (50) and the inner container (30) therein; and heating means (70) arranged outside the outer container (60) and configured to heat the cavity (5), wherein the inner container (30) comprises a support structure for supporting a solid monolithic source material (10) at a predetermined distance above the substrate (20) in the cavity (5) such that a growth surface of the substrate (20) is entirely exposed to the source material (10). A corresponding method is also disclosed.